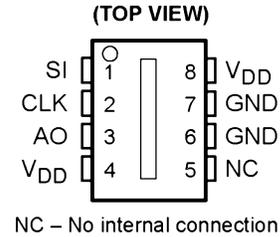


# TSL213 64 × 1 INTEGRATED OPTO SENSOR

SOES009A – D4059, NOVEMBER 1992 – REVISED AUGUST 1993

- Contains 64-Bit Static Shift Register
- Contains Analog Buffer With Sample and Hold for Analog Output Over Full Clock Period
- Single-Supply Operation
- Operates With 500-kHz Shift Clock
- 8-Pin Clear Plastic DIP Package
- Advanced LinCMOS™ Technology



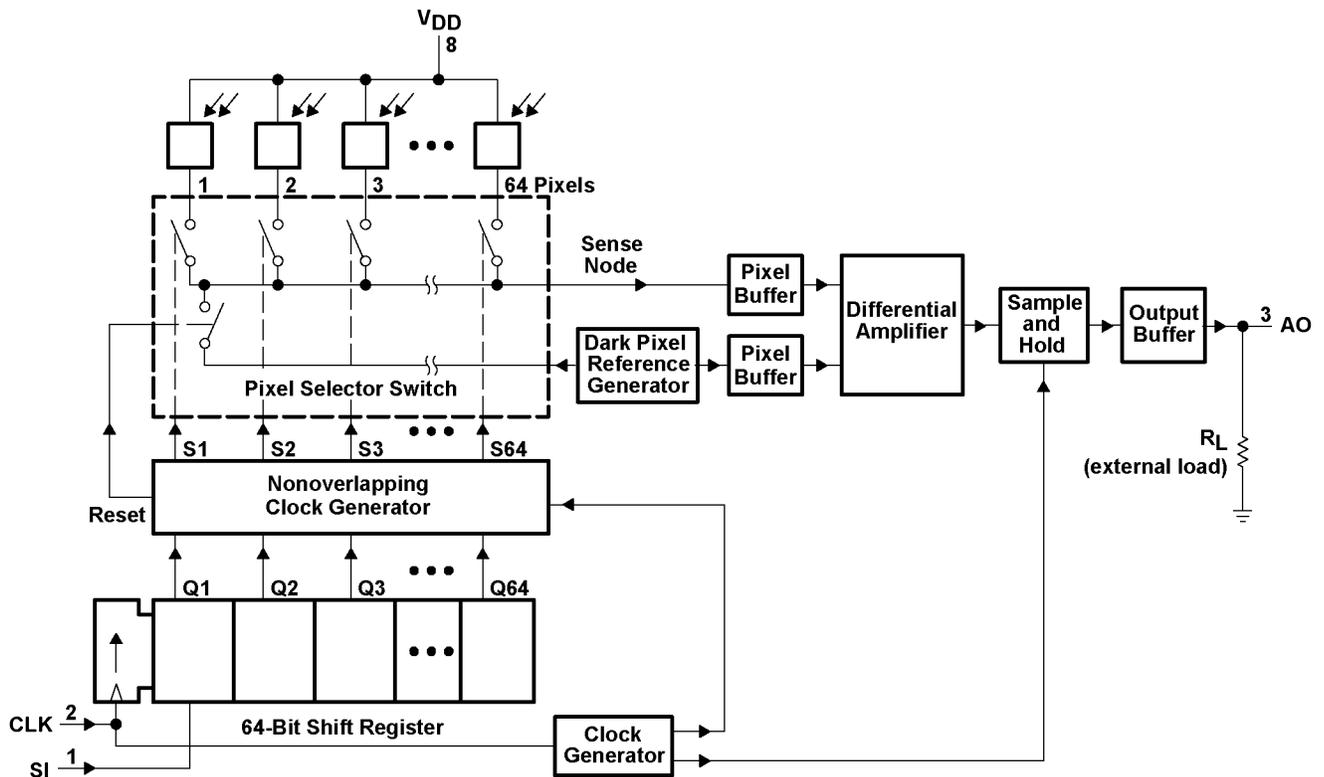
## description

The TSL213 integrated opto sensor consists of 64 charge-mode pixels arranged in a 64 × 1 linear array. Each pixel measures 120 μm × 70 μm with 125-μm center-to-center spacing. Operation is simplified by internal logic requiring only clock and start-integration-pulse signals.

The TSL213 is intended for use in a wide variety of applications including linear and rotary encoding, linear positioning, edge and mark detection, and contact imaging.

The TSL213 is supplied in an 8-pin dual-in-line clear plastic package.

## functional block diagram



Caution. These devices have limited built-in gate protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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# TSL213

## 64 × 1 INTEGRATED OPTO SENSOR

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### Terminal Functions

PIN		DESCRIPTION
NAME	NO.	
AO	3	Analog output
CLK	2	Clock. The clock controls charge transfer, pixel output, and reset.
GND	6, 7	Ground (substrate). All voltages are referenced to the substrate.
NC	5	No internal connection
SI	1	Serial input. The serial input defines the end of the integration period and initiates the pixel output sequence.
VDD	4, 8	Supply voltages. These supply power to the analog and digital circuits.

### detailed description

#### sensor elements

The line of sensor elements, called pixels, consists of 64 discrete photosensing areas. Light energy striking a pixel generates electron-hole pairs in the region under the pixel. The field generated by the bias on the pixel causes the electrons to collect in the element while the holes are swept into the substrate. The amount of charge accumulated in each element is directly proportional to the amount of incident light and the integration time.

#### device operation

Operation of the 64 × 1 array sensor consists of two time periods: an integration period during which charge is accumulated in the pixels and an output period during which signals are transferred to the output. The integration period is defined by the interval between serial-input (SI) pulses and includes the output period (see Figure 1). The required length of the integration period depends upon the amount of incident light and the desired output signal level.

#### sense node

On completion of the integration period, the charge contained in each pixel is transferred in turn to the sense node under the control of the clock (CLK) and SI signals. The signal voltage generated at this node is directly proportional to the amount of charge and inversely proportional to the capacitance of the sense node.

#### reset

An internal reset signal is generated by the nonoverlapping clock generator (NOCG) and occurs every clock cycle. Reset establishes a known voltage on the sense node in preparation for the next charge transfer. This voltage is used as a reference level for the differential signal amplifier.

#### shift register

The 64-bit shift register controls the transfer of charge from the pixels to the output stages and provides timing signals for the NOCG. The SI signal provides the input to the shift register and is shifted under direct control of the clock.

The output period is initiated by the presence of the SI input pulse coincident with a rising edge of CLK (see Figures 1 and 2). The analog output voltage corresponds to the level of the first pixel after settling time ( $t_s$ ) and remains constant for a minimum time,  $t_v$ . A voltage corresponding to each succeeding pixel is available at each rising edge of the clock. The output period ends on the rising edge of the 65th clock cycle, at which time the output assumes the high-impedance state. The 65th clock cycle terminates the output of the last pixel and clears the shift register in preparation for the next SI pulse. To achieve minimum integration time, the SI pulse may be present on the 66th rising edge of the clock to immediately reinitiate the output phase. When the output period has been initiated by an SI pulse, the clock must be allowed to complete 65 positive-going transitions in order to reset the internal logic to a known state.

**sample and hold**

The sample-and-hold signal generated by the NOCG is used to hold the analog output voltage of each pixel constant until the next pixel is clocked out. The signal is sampled while CLK is high and held constant while CLK is low.

**nonoverlapping clock generators**

The NOCG circuitry provides internal control signals for the sensor, including reset and pixel-charge sensing. The signals are synchronous and are controlled by the outputs of the shift register.

**initialization**

Initialization of the sensor elements may be necessary on power up or during operation after any period of clock or SI inactivity exceeding the integration time. The initialization phase consists of 12 to 15 consecutively performed output cycles and clears the pixels of any charge that may have accumulated during the inactive period.

**output enable**

The internally-generated output-enable signal enables the output stage of the sensor during the output period (64 clock cycles). During the remainder of the integration period, the output stage is in the high-impedance state that allows output interconnections of multiple devices without interference.

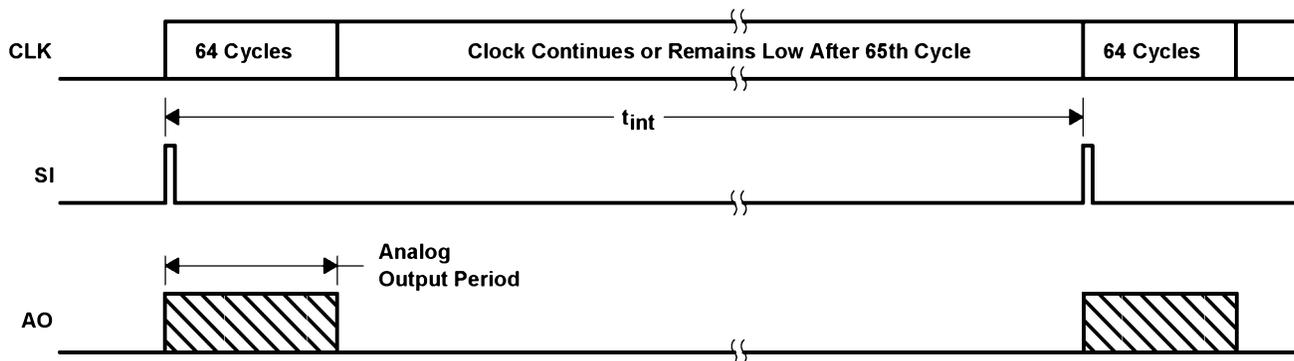


Figure 1. Timing Waveforms

**absolute maximum ratings,  $T_A = 25^\circ\text{C}$  (unless otherwise noted) (see Note 1)†**

Supply voltage range, $V_{DD}$ .....	-0.5 V to 7 V
Digital input current range, $I_I$ .....	-20 mA to 20 mA
Operating case temperature range, $T_C$ (see Note 2) .....	-10°C to 85°C
Operating free-air temperature range, $T_A$ .....	0°C to 70°C
Storage temperature range .....	-25°C to 85°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds .....	260°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Voltage values are with respect to the network GND.

2. Case temperature is the surface temperature of the plastic package measured directly over the integrated circuit.

# TSL213

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### recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, $V_{DD}$	4.5		5.5	V
Input voltage, $V_I$	0		$V_{DD}$	V
High-level input voltage, $V_{IH}$	$V_{DD} \times 0.7$		$V_{DD}$	V
Low-level input voltage, $V_{IL}$	0		$V_{DD} \times 0.3$	V
Wavelength of light source, $\lambda$		750		nm
Clock input frequency, $f_{clock}$	10		500	kHz
Pulse duration, CLK low, $t_W$	1			$\mu$ s
Sensor integration time, $t_{int}$		5		ms
Setup time, SI before $CLK\uparrow$ , $t_{su}(SI)$	50			ns
Hold time, SI after $CLK\uparrow$ , $t_h(SI)$	50			ns
External resistive load, AO, $R_L$		330		$\Omega$
Total number of TSL213 outputs connected together			10	
Operating free-air temperature, $T_A$	0		70	$^{\circ}$ C

**electrical characteristics,  $V_{DD} = 5$  V,  $T_A = 25^{\circ}$ C,  $f_{clock} = 180$  kHz,  $\lambda_p = 565$  nm,  $R_L = 330$   $\Omega$ ,  $C_L = 330$  pF,  $t_{int} = 5$  ms,  $E_e = 20$   $\mu$ W/cm<sup>2</sup> (unless otherwise noted) (see Note 3)**

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Analog output voltage saturation level	$E_e = 51$ $\mu$ W/cm <sup>2</sup>	3	3.4		V
Analog output voltage (white, average over 64 pixels)		1.75	2		V
Analog output voltage (dark, each pixel)	$E_e = 0$		0.25	0.4	V
Output voltage (white) change with change in $V_{DD}$	$V_{DD} = 5$ V $\pm 5\%$		$\pm 2\%$		
Dispersion of analog output voltage	See Note 4			$\pm 10\%$	
Linearity of analog output voltage	See Note 5	0.85		1.15	
Pixel recovery time	See Note 6		25	40	ms
Supply current	$I_{DD}$ Avg		4	9	mA
High-level input current	$V_I = V_{DD}$			0.5	$\mu$ A
Low-level input current	$V_I = 0$			0.5	$\mu$ A
Input capacitance			5		pF

NOTES: 3. The input irradiance ( $E_e$ ) is supplied by an LED array with  $\lambda_p = 565$  nm.

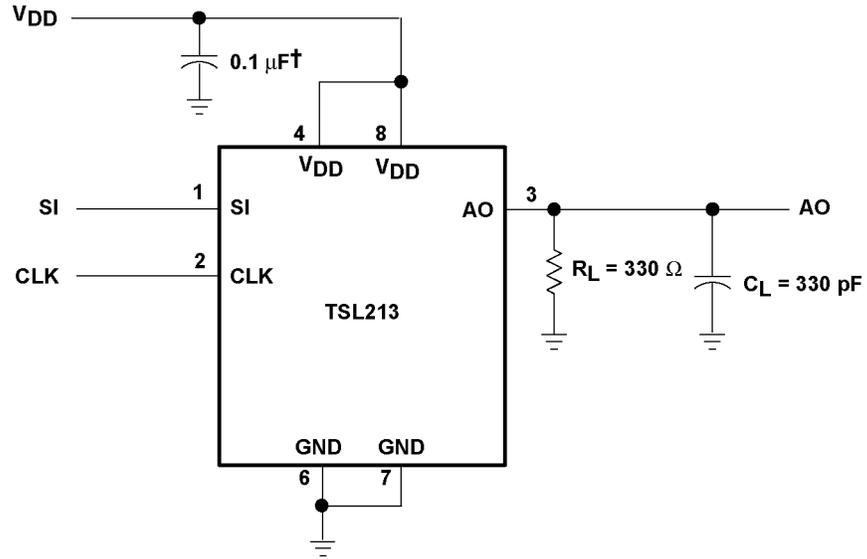
- Dispersion of analog output voltage is the maximum difference between the voltage from any single pixel and the average output voltage from all pixels of the device under test.
- Linearity of analog output voltage is calculated by averaging over 64 pixels and measuring the maximum deviation of the voltage at 2 ms and 3.5 ms from a line drawn between the voltage at 2.5 ms and the voltage at 5 ms.
- Pixel recovery time is the time required for a pixel to go from the analog-output-voltage (white, average over 64 pixels) level to the analog-output-voltage (dark, each pixel) level or vice versa after a step change in light input.

**operating characteristics,  $V_{DD} = 5$  V,  $T_A = 25^{\circ}$ C,  $R_L = 330$   $\Omega$ ,  $C_L = 330$  pF,  $t_{int} = 5$  ms,  $E_e = 20$   $\mu$ W/cm<sup>2</sup>,  $f_{clock} = 500$  kHz (unless otherwise noted)**

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_s$ Settling time	See Figure 2 and Note 7			1	$\mu$ s
$t_v$ Valid time				$1/2 f_{clock}$	$\mu$ s

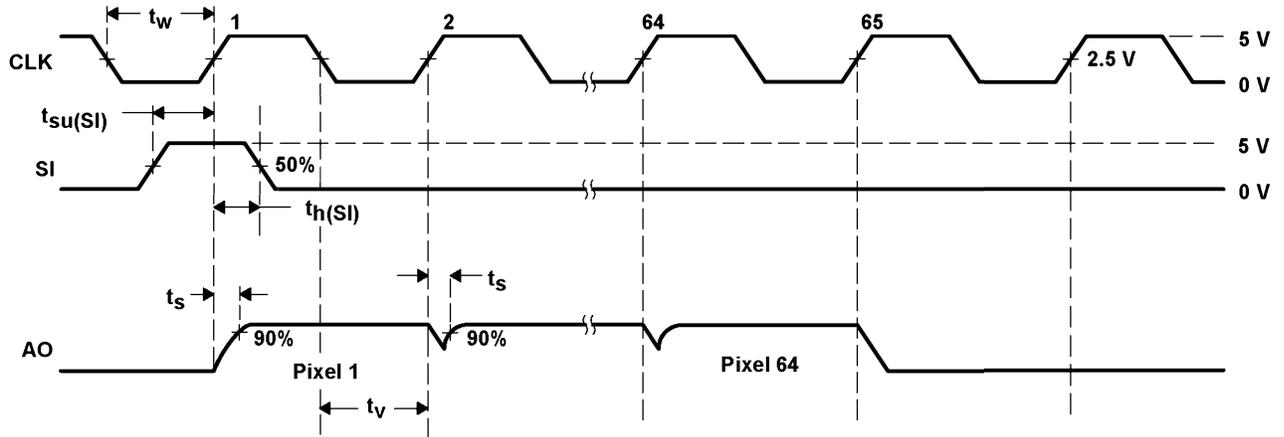
NOTE 7: Clock duty cycle is assumed to be 50%.

PARAMETER MEASUREMENT INFORMATION



† Supply bypass capacitor with short leads should be placed as close to the device as possible.

TEST CIRCUIT



OPERATIONAL WAVEFORMS

Figure 2. Test Circuit and Operational Waveforms

# TSL213

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### TYPICAL CHARACTERISTICS

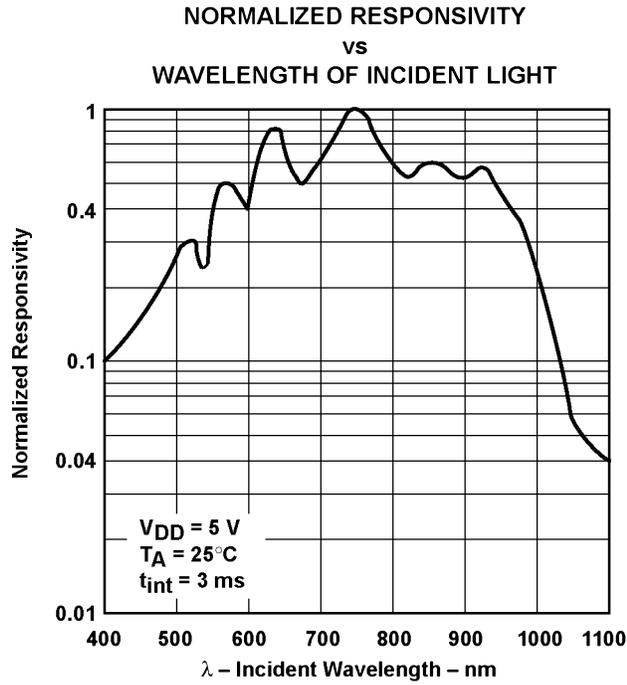


Figure 3

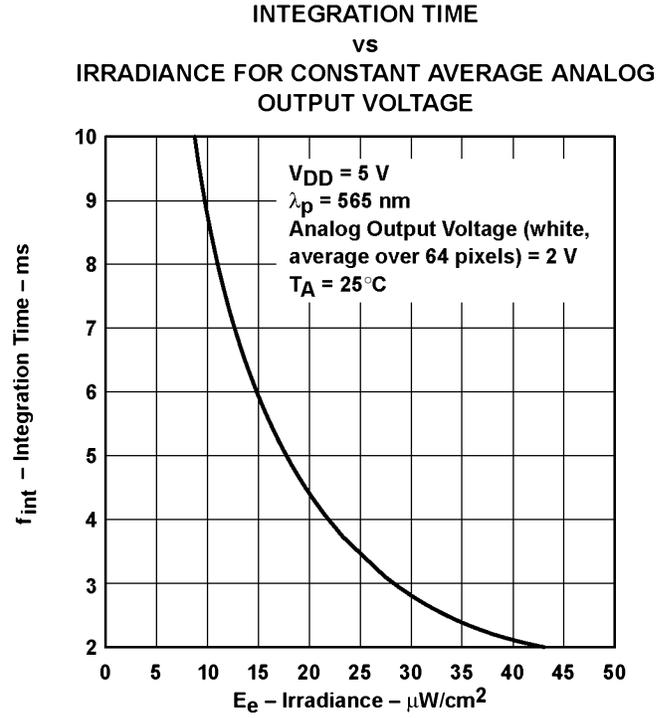


Figure 4

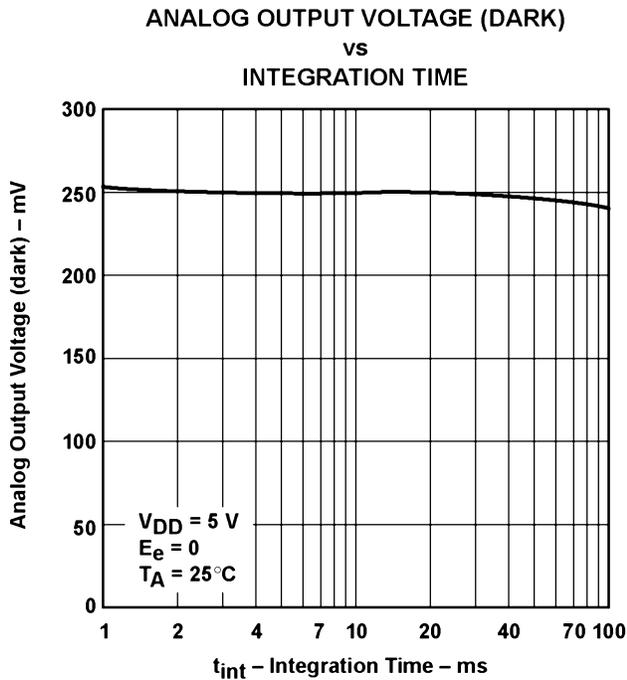


Figure 5

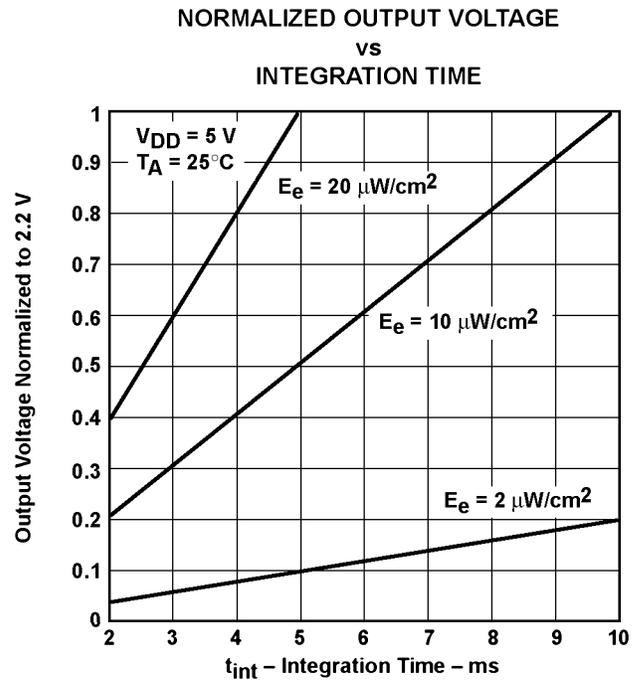


Figure 6



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